International
IOR Rectifier

Bulletin I0122J rev. A 02/97

IR135DM12CCB

STANDARD RECOVERY DIODES

- **Junction Size:** **Rectangular 135 x 100 mils**
- **Wafer Size:** **4"**
- **V_{RRM} Class:** **1200 V**
- **Passivation Process:** **Glassivated MOAT**
- **Reference IR Packaged Part:** **8EWS..S Series**

Major Ratings and Characteristics

Parameters		Units	Test Conditions
V_{FM}	Maximum Forward Voltage	1.1 V	$T_J = 25°C$, $I_F = 8$ A
V_{RRM}	Reverse Breakdown Voltage	1200 V	$T_J = 25°C$, $I_{RRM} = 100$ µA **(1)**

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 µm)
Chip Dimensions	135 x 100 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 µm, ± 10 µm
Maximum Width of Sawing Line	45 µm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

IR	135	D	M	12	C	CB
1	2	3	4	5	6	7

1 - International Rectifier Device

2 - Chip Dimension in Mils

3 - Type of Device: D = Wire Bondable Standard Recovery Diode

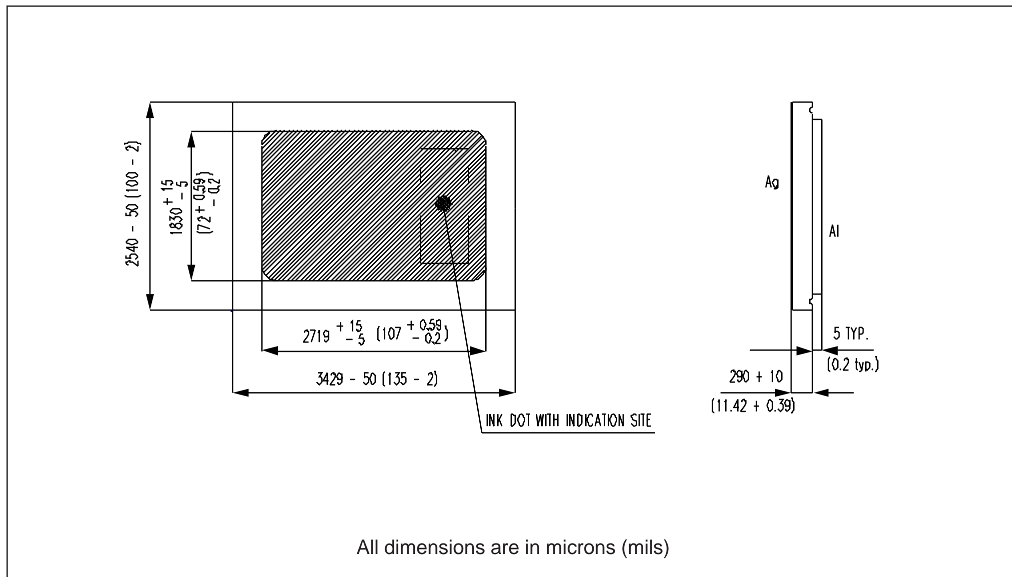
4 - Passivation Process: M = Glassivated MOAT

5 - Voltage code: Code x 100 = V_{RRM}

6 - Metallization: C = Aluminium (Anode) - Silver (Cathode)

7 - CB = Probed Uncut Die (wafer in box)
None = Probed Die in chip carrier

Outline Table

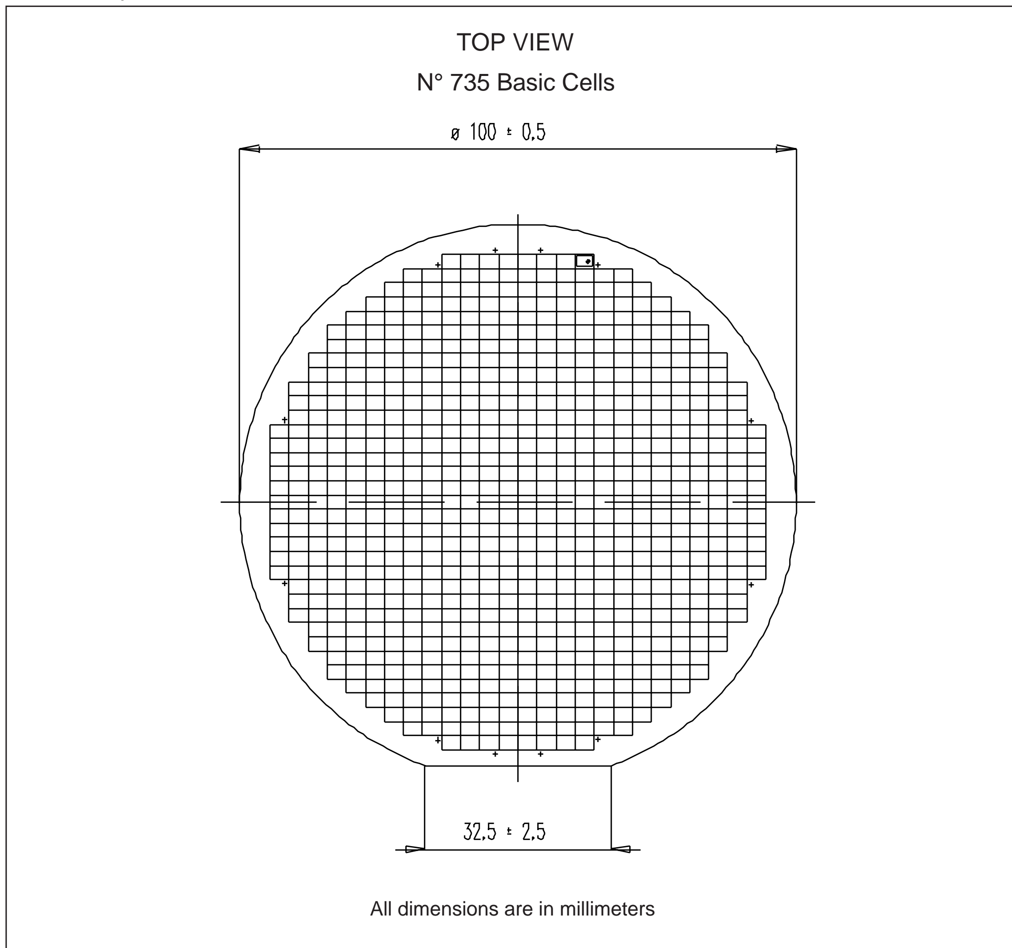


All dimensions are in microns (mils)

Wafer Layout

TOP VIEW

N° 735 Basic Cells



All dimensions are in millimeters